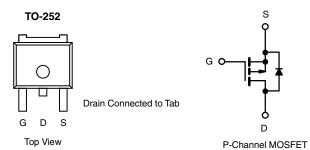


www.vishay.com

Vishay Siliconix

# Automotive P-Channel 80 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	- 80		
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 \text{ V}$	0.025		
$R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 \text{ V}$	0.031		
I <sub>D</sub> (A)	- 50		
Configuration	Single		



### **FEATURES**

- TrenchFET® Power MOSFET
- AEC-Q101 Qualifiedd
- 100 % R<sub>a</sub> and UIS Tested
- Material categorization:
   For definitions of compliance please see www.vishay.com/doc?99912



FREE

ORDERING INFORMATION	
Package	TO-252
Lead (Pb)-free and Halogen-free	SQD50P08-25L-GE3

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>C</sub> = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		$V_{DS}$	- 80	V	
Gate-Source Voltage		V <sub>GS</sub>	± 20	V	
Continuous Drain Current	T <sub>C</sub> = 25 °C <sup>a</sup>	L	- 50		
	T <sub>C</sub> = 125 °C	- I <sub>D</sub>	- 28		
Continuous Source Current (Diode Conducti	Is	- 50	Α		
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	- 120		
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	- 45		
Single Pulse Avalanche Energy	L = 0.1 IIII1	E <sub>AS</sub>	100	mJ	
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 25 °C	P <sub>D</sub>	136	W	
	T <sub>C</sub> = 125 °C		45	VV	
Operating Junction and Storage Temperatur	e Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount <sup>c</sup>	$R_{thJA}$	50	°C/W	
Junction-to-Case (Drain)		$R_{thJC}$	1.1	C/VV	

### Notes

- a. Package limited.
- b. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.



# Vishay Siliconix

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static							,	
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$		- 80	-	-	V	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = - 250 μA		- 2.0	- 2.5	V	
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$0 \text{ V}, \text{ V}_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA	
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = - 80 V	-	-	- 1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = - 80 V, T <sub>J</sub> = 125 °C	-	-	- 50	μΑ	
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = - 80 V, T <sub>J</sub> = 175 °C	-	-	- 250		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = - 10 V	V <sub>DS</sub> ≤ - 5 V	- 50	-	-	Α	
		V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 12.5 A	-	0.020	0.025		
Drain Cauras On State Besistance	В	V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 12.5 A, T <sub>J</sub> = 125 °C	-	-	0.044	Ω	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 12.5 A, T <sub>J</sub> = 175 °C	-	-	0.055		
		V <sub>GS</sub> = - 4.5 V	I <sub>D</sub> = - 10.5 A	-	0.025	0.031		
Forward Transconductanceb	9 <sub>fs</sub>	V <sub>DS</sub> = -	V <sub>DS</sub> = - 15 V, I <sub>D</sub> = - 12.5 A		38	-	S	
Dynamic <sup>b</sup>								
Input Capacitance	C <sub>iss</sub>		V <sub>DS</sub> = - 25 V, f = 1 MHz	-	4279	5350	pF	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$		-	356	445		
Reverse Transfer Capacitance	C <sub>rss</sub>			-	239	300		
Total Gate Charge <sup>c</sup>	Qg			-	91	137		
Gate-Source Charge <sup>c</sup>	$Q_{gs}$	V <sub>GS</sub> = - 10 V	$V_{DS} = -40 \text{ V}, I_{D} = -12.5 \text{ A}$	-	8.2	-	nC	
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$			-	24	-		
Gate Resistance	R <sub>g</sub>	f = 1 MHz		1.60	3.26	5.00	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			-	10	15		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = \text{- 40 V},  R_L = 3.2  \Omega$ $I_D \cong \text{- 12.5 A},  V_{GEN} = \text{- 10 V},  R_g = 1  \Omega$		-	11	17	ns	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			-	71	107		
Fall Time <sup>c</sup>	t <sub>f</sub>			-	16	24		
Source-Drain Diode Ratings and Chara	acteristics <sup>b</sup>							
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	- 120	Α	
Forward Voltage	$V_{SD}$	I <sub>F</sub> = - 10.5 A, V <sub>GS</sub> = 0 V		-	- 0.82	- 1.5	V	

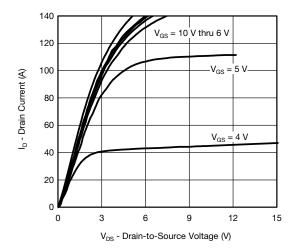
### Notes

- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

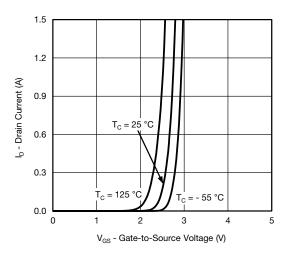
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



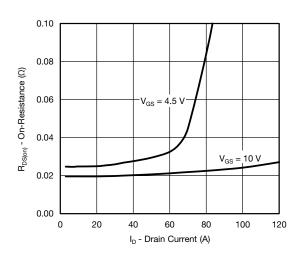
### TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)



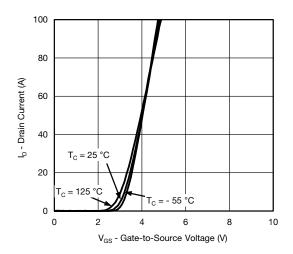
### **Output Characteristics**



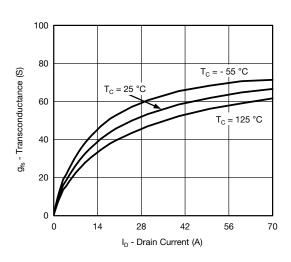
### **Transfer Characteristics**



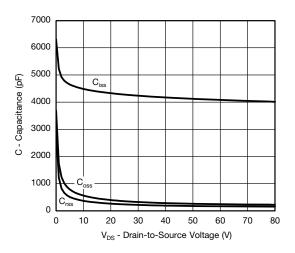
On-Resistance vs. Drain Current



### **Transfer Characteristics**



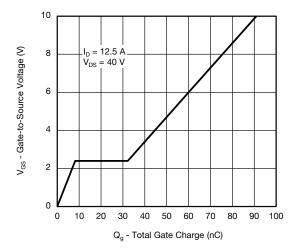
### Transconductance



Capacitance

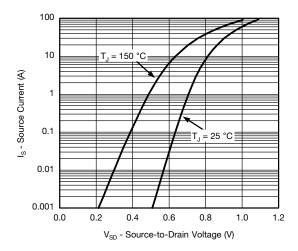


### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)

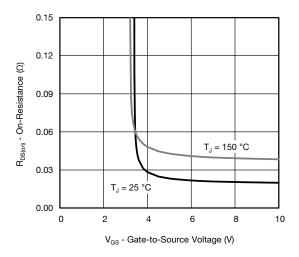


### 2.5 $I_D = 12.5 A$ R<sub>DS(on)</sub> - On-Resistance (Normalized) 2.1 $V_{GS} = 10$ 1.7 $V_{GS} = 4.5 \text{ V}$ 1.3 0.9 0.5 - 25 - 50 0 25 50 100 125 T<sub>J</sub> - Junction Temperature (°C)

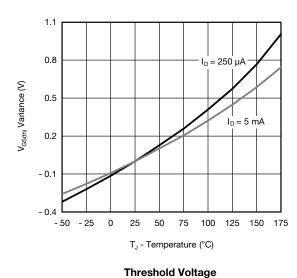
### **Gate Charge**



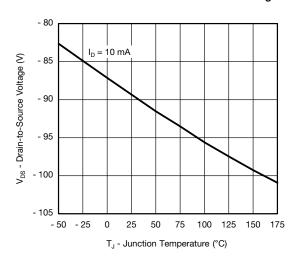
### On-Resistance vs. Junction Temperature



### **Source Drain Diode Forward Voltage**



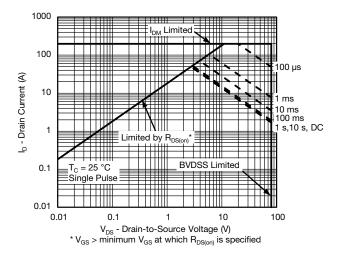
On-Resistance vs. Gate-to-Source Voltage



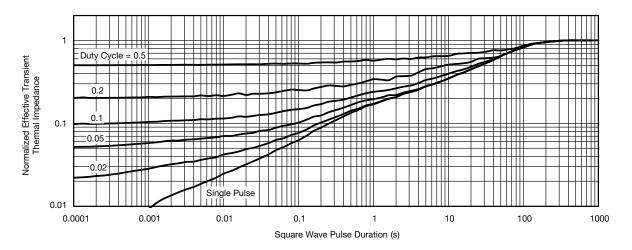
**Drain Source Breakdown vs. Junction Temperature** 



### **THERMAL RATINGS** ( $T_A = 25$ °C, unless otherwise noted)

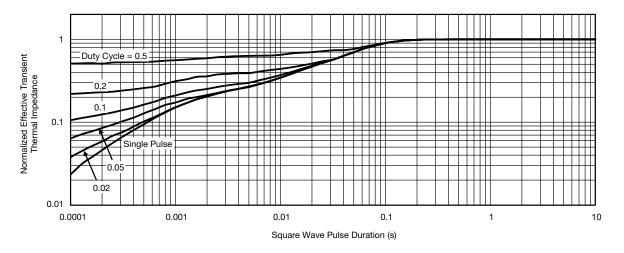


### Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

### **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



#### Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?72217.

Vishay Siliconix

## DPAK / TO-252 and Reverse DPAK

Ordering codes for the SQ rugged series power MOSFETs in the DPAK / TO-252 and Reverse DPAK packages:

DATASHEET PART NUMBER	OLD ORDERING CODE a	<b>NEW ORDERING CODE</b>
SQD07N25-350H	SQD07N25-350H-GE3	SQD07N25-350H_GE3
SQD100N03-3m2L	SQD100N03-3M2L-GE3	SQD100N03-3M2L_GE3
SQD100N03-3m4	SQD100N03-3M4-GE3	SQD100N03-3M4_GE3
SQD100N04-3m6	SQD100N04-3M6-GE3	SQD100N04-3M6_GE3
SQD100N04-3m6L	SQD100N04-3M6L-GE3	SQD100N04-3M6L_GE3
SQD10N30-330H	SQD10N30-330H-GE3	SQD10N30-330H_GE3
SQD15N06-42L	SQD15N06-42L-GE3	SQD15N06-42L_GE3
SQD19P06-60L	SQD19P06-60L-GE3	SQD19P06-60L_GE3
SQD23N06-31L	SQD23N06-31L-GE3	SQD23N06-31L_GE3
SQD25N06-22L	SQD25N06-22L-GE3	SQD25N06-22L_GE3
SQD25N15-52	SQD25N15-52-GE3	SQD25N15-52_GE3
SQD30N05-20L	SQD30N05-20L-GE3	SQD30N05-20L_GE3
SQD40N06-14L	SQD40N06-14L-GE3	SQD40N06-14L_GE3
SQD40N10-25	SQD40N10-25-GE3	SQD40N10-25_GE3
SQD40P10-40L	SQD40P10-40L-GE3	SQD40P10-40L_GE3
SQD45P03-12	SQD45P03-12-GE3	SQD45P03-12_GE3
SQD50N04-5m6	SQD50N04-5M6-GE3	SQD50N04-5M6_GE3
SQD50N05-11L	SQD50N05-11L-GE3	SQD50N05-11L_GE3
SQD50N06-09L	SQD50N06-09L-GE3	SQD50N06-09L_GE3
SQD50N10-8m9L	SQD50N10-8M9L-GE3	SQD50N10-8M9L_GE3
SQD50P03-07	SQD50P03-07-GE3	SQD50P03-07_GE3
SQD50P04-13L	SQD50P04-13L-GE3	SQD50P04-13L_GE3
SQD50P04-09L	SQD50P04-09L-GE3	SQD50P04-09L_GE3
SQD50P06-15L	SQD50P06-15L-GE3	SQD50P06-15L_GE3
SQD50P08-25L	SQD50P08-25L-GE3	SQD50P08-25L_GE3
SQD50P08-28	SQD50P08-28-GE3	SQD50P08-28_GE3
SQD90P04-9m4L	SQD90P04-9M4L-GE3	SQD90P04-9M4L_GE3
SQD97N06-6m3L	SQD97N06-6M3L-GE3	SQD97N06-6M3L_GE3
SQR40N10-25	SQR40N10-25-GE3	SQR40N10-25_GE3
SQR50N04-3m8	SQR50N04-3M8-GE3	SQR50N04-3M8_GE3

### Note

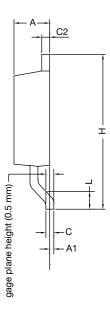
a. Old ordering code is obsolete and no longer valid for new orders



Vishay Siliconix

## **TO-252AA Case Outline**





	MILLIMETERS		INCHES		
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	2.18	2.38	0.086	0.094	
A1	-	0.127	-	0.005	
b	0.64	0.88	0.025	0.035	
b2	0.76	1.14	0.030	0.045	
b3	4.95	5.46	0.195	0.215	
С	0.46	0.61	0.018	0.024	
C2	0.46	0.89	0.018	0.035	
D	5.97	6.22	0.235	0.245	
D1	4.10	-	0.161	-	
E	6.35	6.73	0.250	0.265	
E1	4.32	-	0.170	-	
Н	9.40	10.41	0.370	0.410	
е	2.28	BSC	0.090 BSC		
e1	4.56 BSC		0.180 BSC		
L	1.40	1.78	0.055	0.070	
L3	0.89	1.27	0.035	0.050	
L4	-	1.02	-	0.040	
L5	1.01	1.52	0.040	0.060	
ECN: T13-0592-Rev. A, 02-Sep-13 DWG: 6019					

### Note

• Dimension L3 is for reference only.



### **RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)**



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index

APPLICATION NOTE



# **Legal Disclaimer Notice**

Vishay

## **Disclaimer**

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

# **Material Category Policy**

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.

Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Vishay documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.

Revision: 02-Oct-12 Document Number: 91000

# **X-ON Electronics**

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET category:

Click to view products by Vishay manufacturer:

Other Similar products are found below:

614233C 648584F IRFD120 JANTX2N5237 2N7000 FCA20N60\_F109 FDZ595PZ 2SK2545(Q,T) 405094E 423220D

TPCC8103,L1Q(CM MIC4420CM-TR VN1206L 614234A 715780A NTNS3166NZT5G SSM6J414TU,LF(T 751625C

IPS70R2K0CEAKMA1 BUK954R8-60E DMN3404LQ-7 NTE6400 SQJ402EP-T1-GE3 2SK2614(TE16L1,Q) 2N7002KW-FAI

DMN1017UCP3-7 EFC2J004NUZTDG ECH8691-TL-W FCAB21350L1 P85W28HP2F-7071 DMN1053UCP4-7 NTE221 NTE2384

NTE2903 NTE2941 NTE2945 NTE2946 NTE2960 NTE2967 NTE2969 NTE2976 NTE455 NTE6400A NTE2910 NTE2916 NTE2956

NTE2911 TK10A80W,S4X(S SSM6P69NU,LF DMP22D4UFO-7B